

NVR5198NL

Power MOSFET

60 V, 155 mΩ, Single N-Channel Logic Level, SOT-23

Features

- Small Footprint Industry Standard Surface Mount SOT-23 Package
- Low $R_{DS(on)}$ for Low Conduction Losses and Improved Efficiency
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\psi J-mb}$ (Notes 1, 2, 3, and 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D 2.2 A
		$T_A = 100^\circ\text{C}$	
Power Dissipation $R_{\psi J-mb}$ (Notes 1 and 3)	Steady State	$T_A = 25^\circ\text{C}$	P_D 1.5 W
		$T_A = 100^\circ\text{C}$	
Continuous Drain Current $R_{\theta JA}$ (Note 1, 2, 3, and 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D 1.7 A
		$T_A = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JA}$ (Notes 1 and 3)	Steady State	$T_A = 25^\circ\text{C}$	P_D 0.9 W
		$T_A = 100^\circ\text{C}$	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 27	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	1.9	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

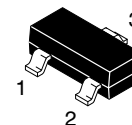
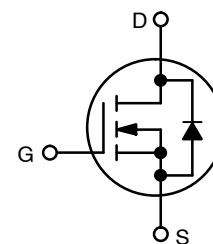


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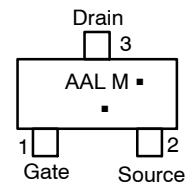
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
60 V	155 mΩ @ 10 V	2.2 A
	205 mΩ @ 4.5 V	

N-Channel



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



AAL = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NVR5198NLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NVR5198NLT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NVR5198NL

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Lead #3 – Drain (Notes 2 and 3)	$R_{\Psi J-mb}$	86	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	139	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	Reference to 25°C , $I_D = 250\text{ }\mu\text{A}$		70		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	Reference to 25°C , $I_D = 250\text{ }\mu\text{A}$		-6.5		mV/°C
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 1\text{ A}$		107	155	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		142	205	
Forward Transconductance	g_{FS}	$V_{DS} = 5.0\text{ V}, I_D = 1\text{ A}$		3		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		182		pF
Output Capacitance	C_{oss}			25		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge	$Q_{G(TOT)}$	$V_{DS} = 48\text{ V}, I_D = 1\text{ A}$	$V_{GS} = 4.5\text{ V}$	2.8		nC
			$V_{GS} = 10\text{ V}$	5.1		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{DS} = 48\text{ V}, I_D = 1\text{ A}, V_{GS} = 10\text{ V}$		0.3		
Gate-to-Source Charge	Q_{GS}			0.8		
Gate-to-Drain Charge	Q_{GD}			1.5		
Plateau Voltage	V_{GP}			3.1		V
Gate Resistance	R_G			8		Ω

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 1\text{ A}, R_G = 10\text{ }\Omega$		5		ns
Rise Time	t_r			7		
Turn-Off Delay Time	$t_{d(off)}$			13		
Fall Time	t_f			2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1 A	T _J = 25°C		0.8	1.2	V
			T _J = 125°C		0.6		
Reverse Recovery Time	t _{rr}	I _S = 1 A _{dc} , V _{GS} = 0 V _{dc} , dI _S /dt = 100 A/μs			12		ns
Charge Time	t _a				9		
Discharge Time	t _b				3		
Reverse Recovery Stored Charge	Q _{RR}				6		nC

5. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

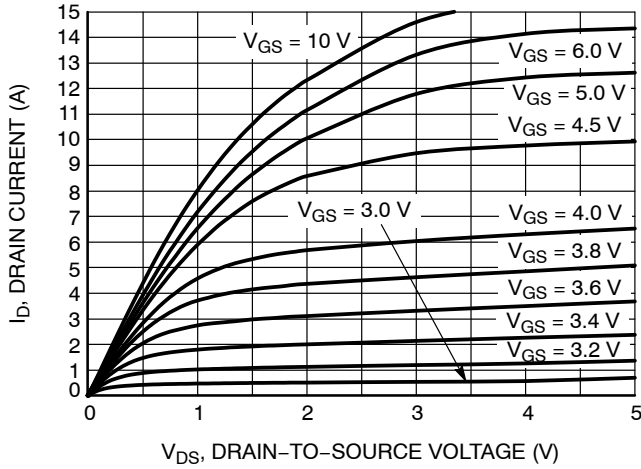


Figure 1. On-Region Characteristics

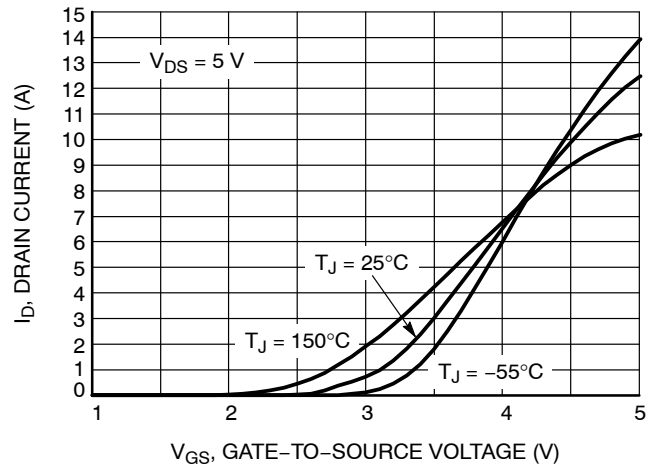


Figure 2. Transfer Characteristics

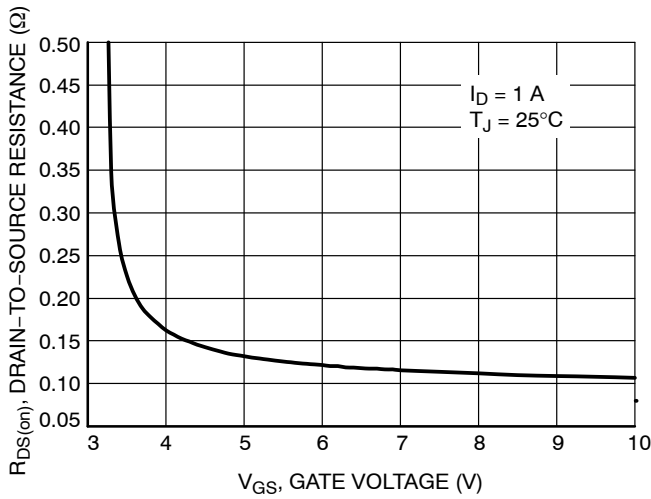


Figure 3. On-Resistance vs. Gate-to-Source Voltage

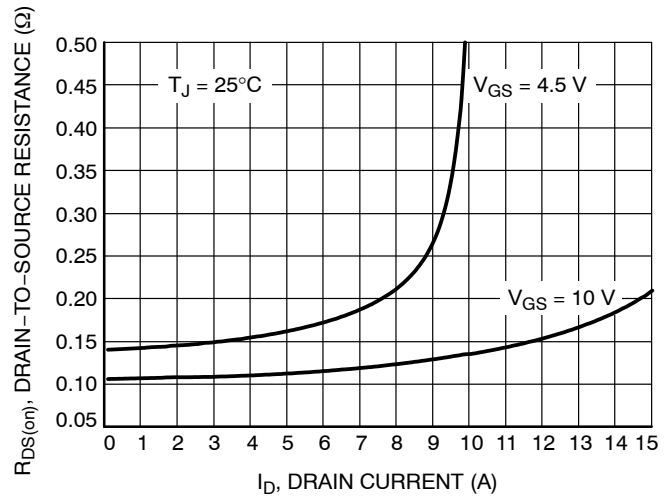


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

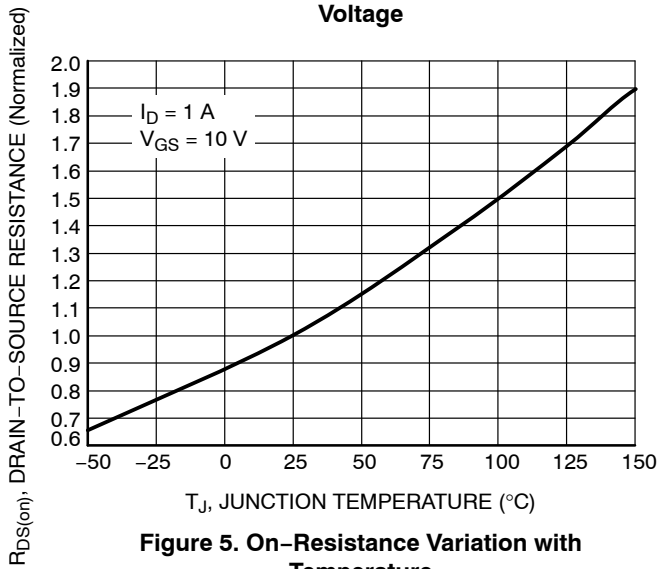


Figure 5. On-Resistance Variation with Temperature

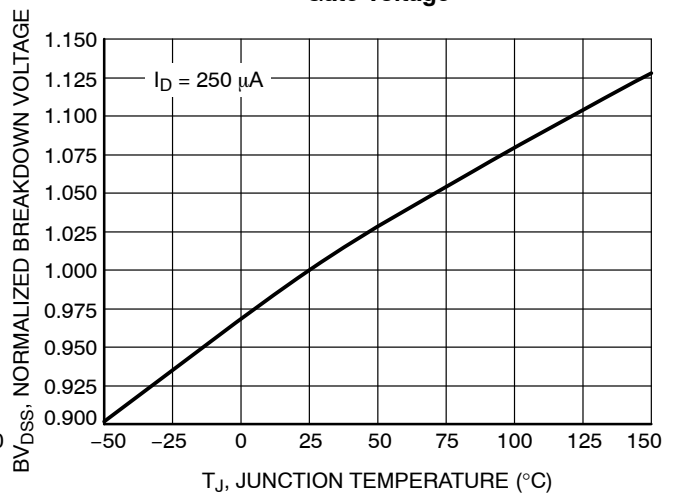


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

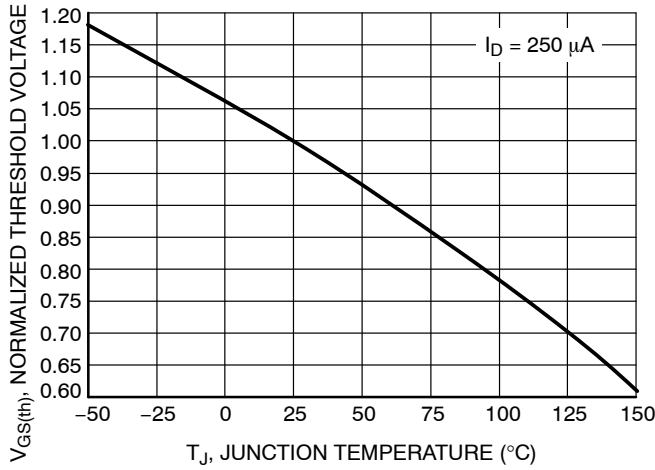


Figure 7. Threshold Voltage Variation with Temperature

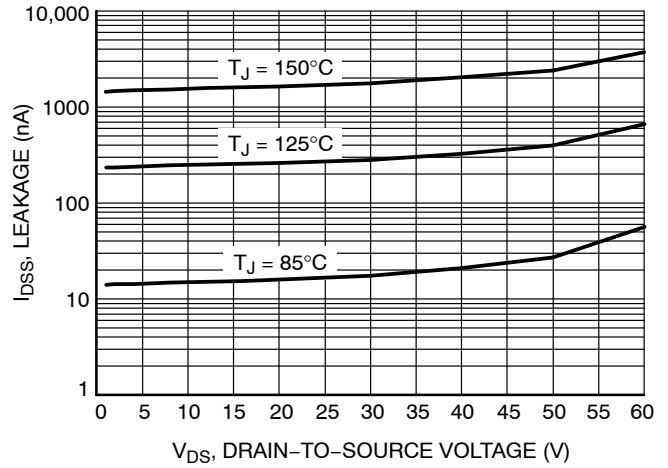


Figure 8. Drain-to-Source Leakage Current vs. Voltage

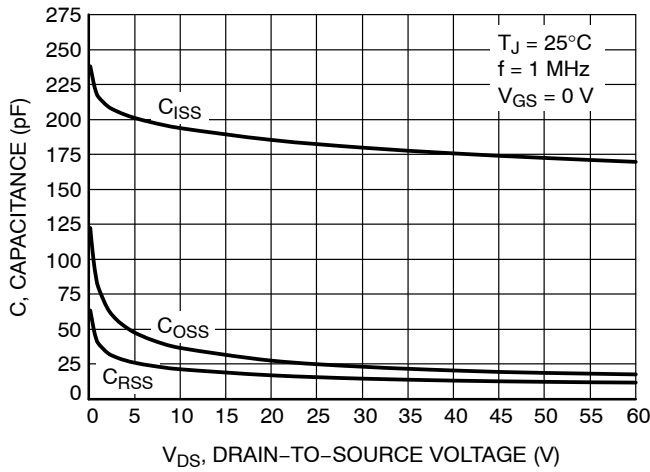


Figure 9. Capacitance Variation

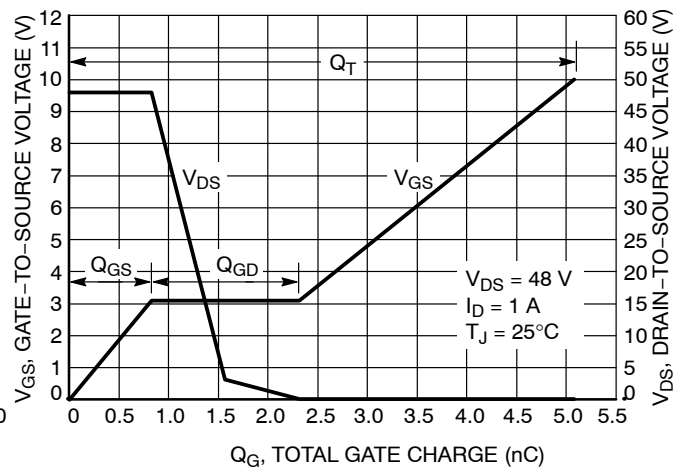


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

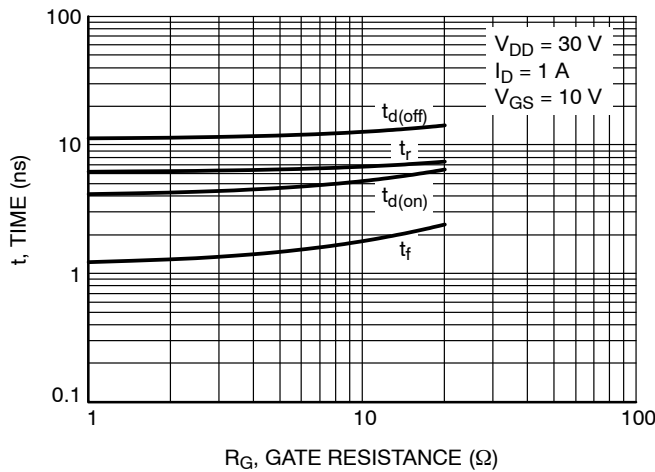


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

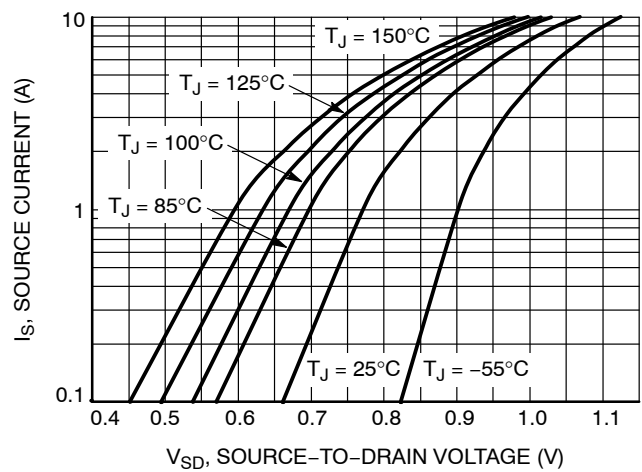


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

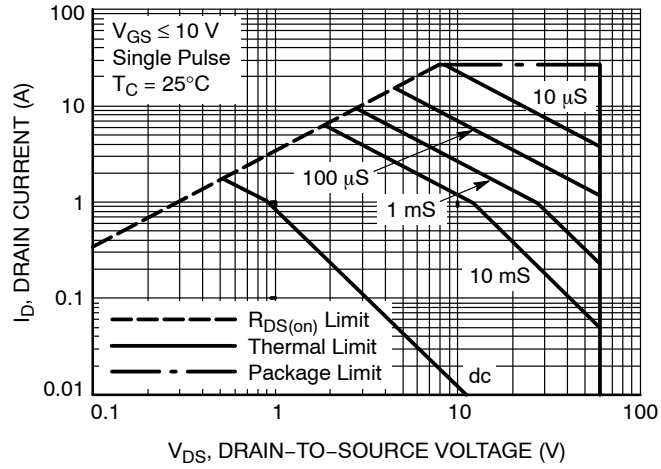


Figure 13. Maximum Rated Forward Biased Safe Operating Area

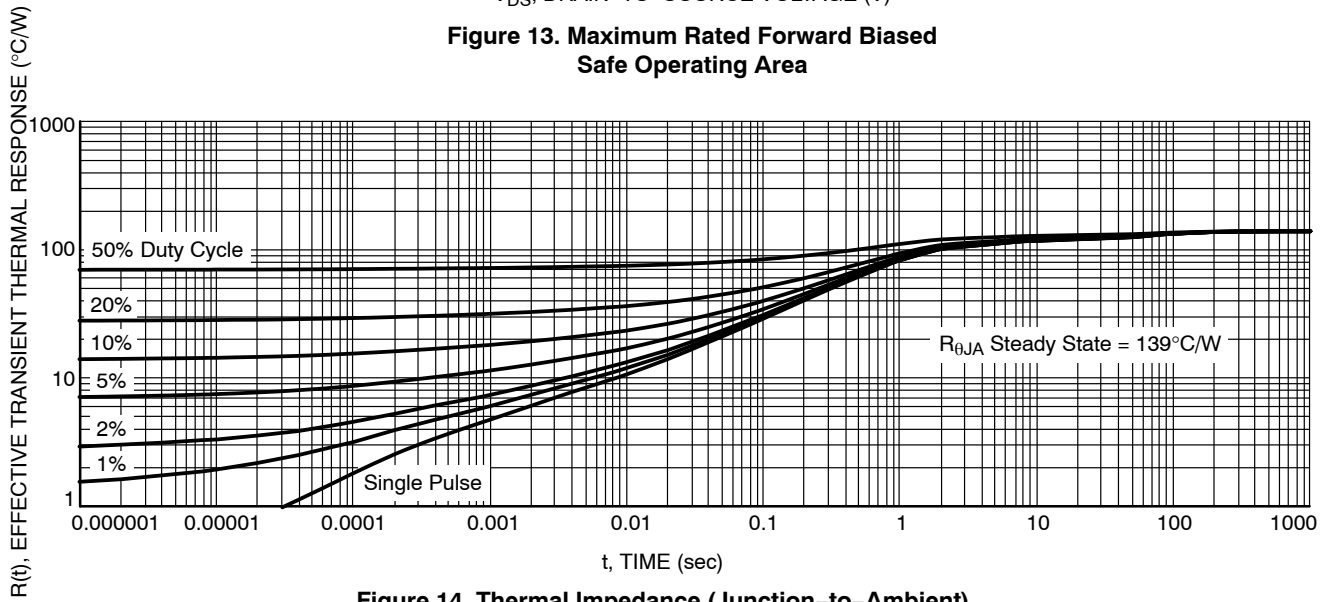
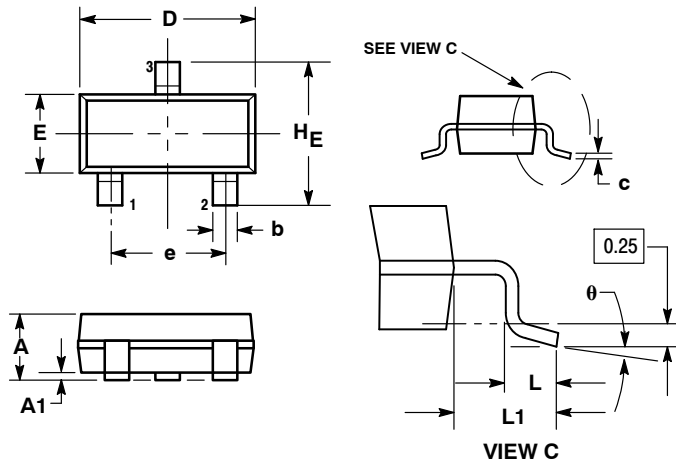


Figure 14. Thermal Impedance (Junction-to-Ambient)

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP

NOTES:

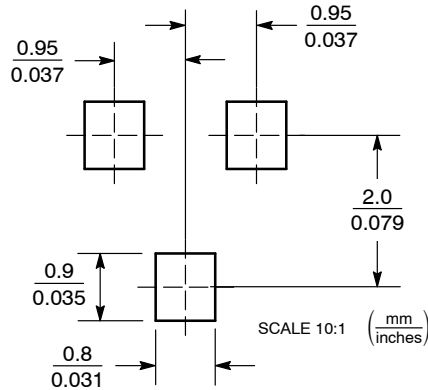
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 21:

- PIN 1. GATE
- SOURCE
- DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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